

<DIODE Modules>

RM800DY-34S

**HIGH POWER SWITCHING USE
INSULATED TYPE**



dual pack

Forward current I_{DC} **800 A**
 Repetitive peak reverse voltage V_{RRM} **1700 V**
 Maximum junction temperature T_{vjmax} **175 °C**

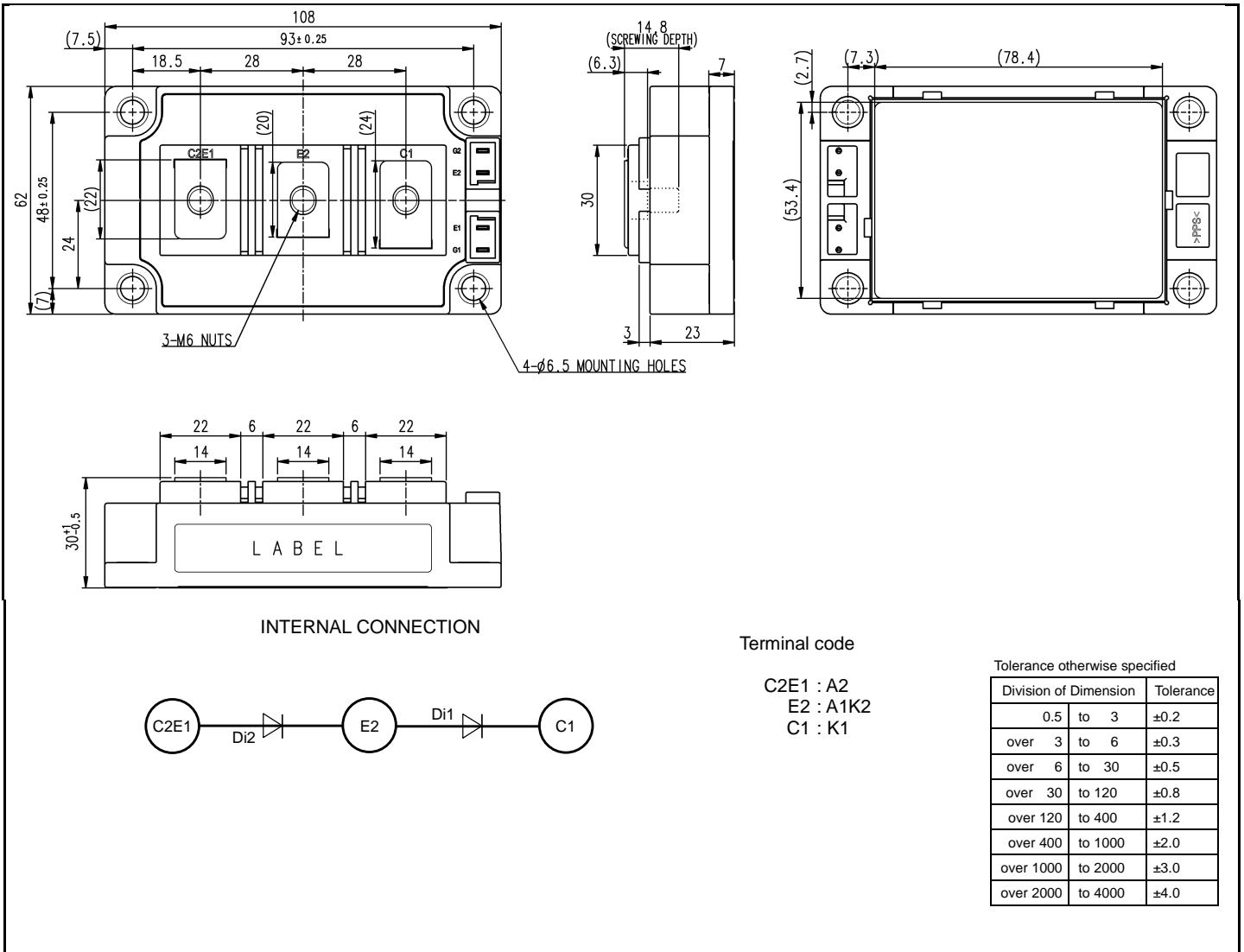
- Flat base Type
- Copper base plate
- RoHS Directive compliant
- UL Recognized under UL1557, File No. E323585

APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, Photovoltaic power, Wind power, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



RM800DY-34SHIGH POWER SWITCHING USE
INSULATED TYPE**MAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Rating	Unit
V _{RRM}	Repetitive peak reverse voltage	-	1700	V
V _{RSM}	Non-repetitive peak reverse voltage	-	1700	V
V _{R(DC)}	Reverse DC blocking voltage	-	1360	V
I _{DC}	Forward current	DC (Note1)	800	A
I _{FSM}	Surge non-repetitive forward current	1 cycle of half wave at 60 Hz, peak value, T _{vj} =25 °C start, V _{RM} =0 V	4000	A
I ² t	Current square time for fusing	t _w =8.3 ms, T _{vj} =25 °C start, Value for one cycle of surge current	6.0 × 10 ⁴	A ² s
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C
T _{Cmax}	Maximum case temperature	(Note2)	125	
T _{vjop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T _{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{RRM}	Reverse current	V _R =V _{RRM} , T _{vj} =150 °C	-	-	50	mA	
V _F (Terminal)	Forward voltage	I _F =800 A, t _w ≤1 ms, Refer to the figure of test circuit	T _{vj} =25 °C	-	2.25	2.75	V
			T _{vj} =125 °C	-	2.35	-	
			T _{vj} =150 °C	-	2.30	-	
V _F (Chip)		I _F =800 A, t _w ≤1 ms	-	2.00	2.50	V	
t _{rr}	Reverse recovery time	V _{CC} =1000 V, I _F =800 A,	-	-	500	ns	
Q _{rr}	Reverse recovery charge	-diF/dt=4000 kA/μs,	-	160	-	μC	
E _{rr}	Reverse recovery energy per pulse	Inductive load	-	104	-	mJ	

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)}	Thermal resistance	Junction to case (Note2)	-	-	20	K/kW
R _{th(c-s)}	Contact thermal resistance	Case to heat sink, Thermal grease applied (Note2, 4)	-	13.3	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M _t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M _s	Mounting torque	Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
d _s	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	-	-	
d _a	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	-	-	
e _c	Flatness of base plate	On the centerline X, Y (Note5)	0	-	+200	μm
m	mass	-	-	260	-	g

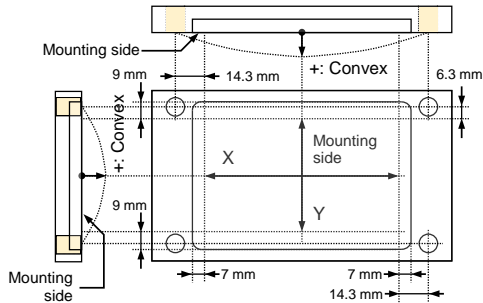
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HIGH POWER SWITCHING USE
 INSULATED TYPE

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

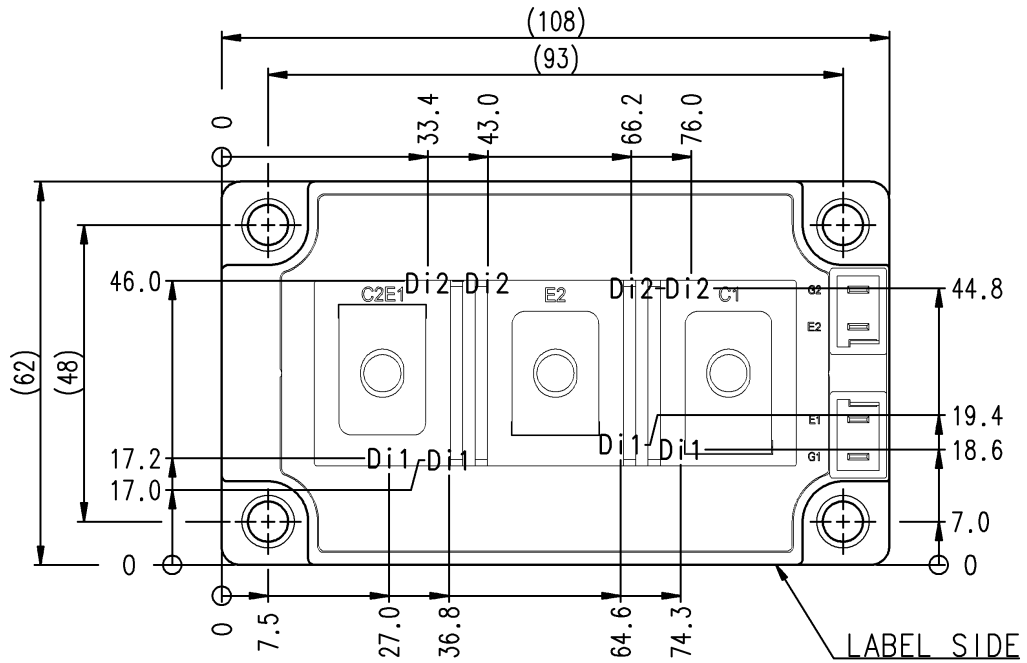
Note1. Junction temperature (T_{vj}) should not exceed T_{vjmax} rating.

2. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
3. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
4. Typical value is measured by using thermally conductive grease of $\lambda=3.0 \text{ W}/(\text{m}\cdot\text{K})/D_{(C-S)}=50 \mu\text{m}$.
5. The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



CHIP LOCATION (Top view)

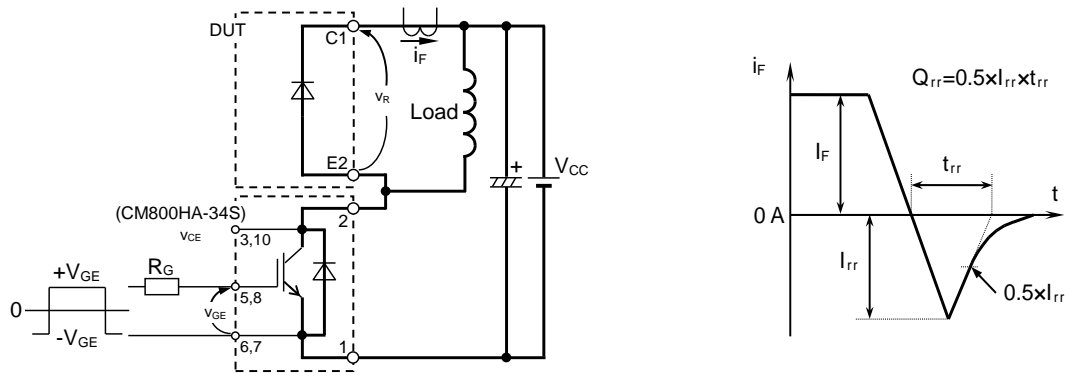
Dimension in mm, tolerance: $\pm 1 \text{ mm}$



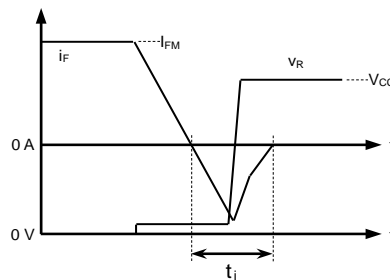
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RM800DY-34S

HIGH POWER SWITCHING USE
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TEST CIRCUIT AND WAVEFORMS

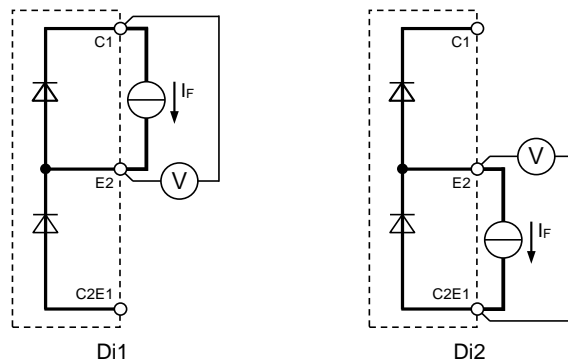


t_{rr} , Q_{rr} characteristics test circuit and waveforms



Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



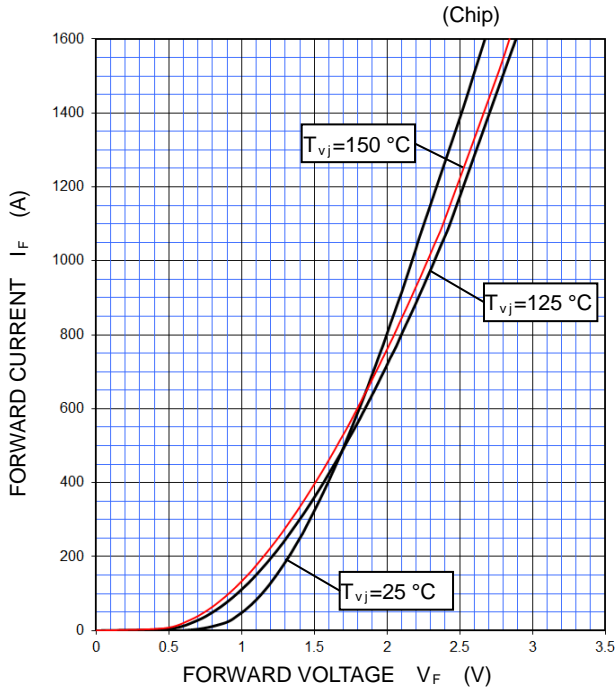
V_F characteristics test circuit

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RM800DY-34S

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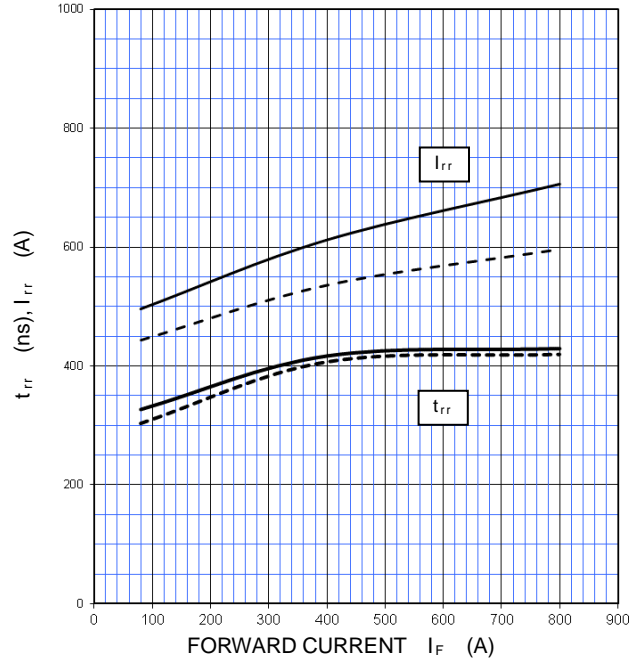
PERFORMANCE CURVES

FORWARD CHARACTERISTICS (TYPICAL)



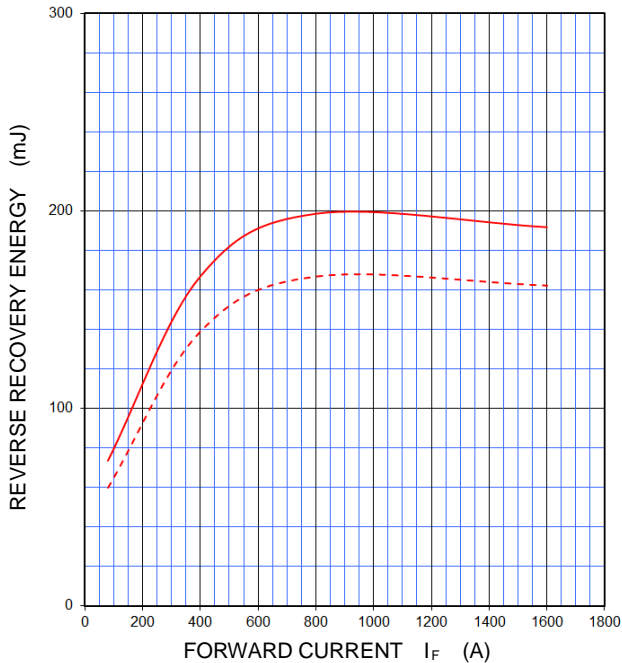
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,
 INDUCTIVE LOAD by using CM800HA-34S
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



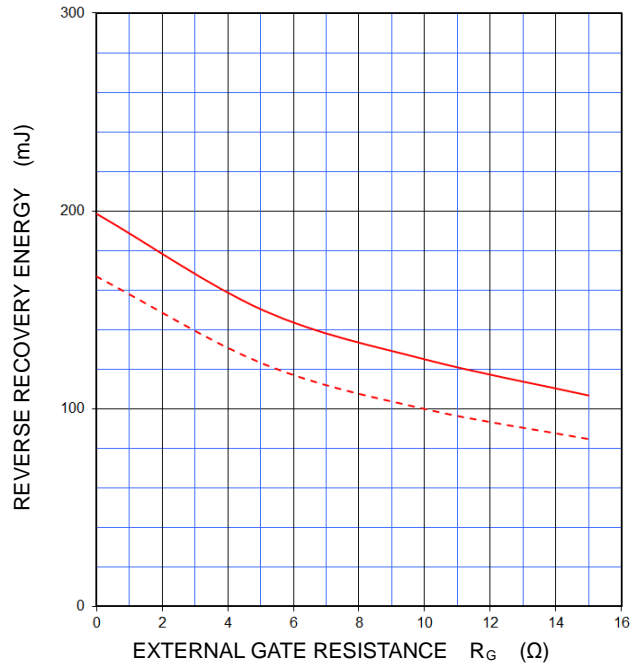
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,
 INDUCTIVE LOAD by using CM800HA-34S, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=1000\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_F=800\text{ A}$,
 INDUCTIVE LOAD by using CM800HA-34S, PER PULSE
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



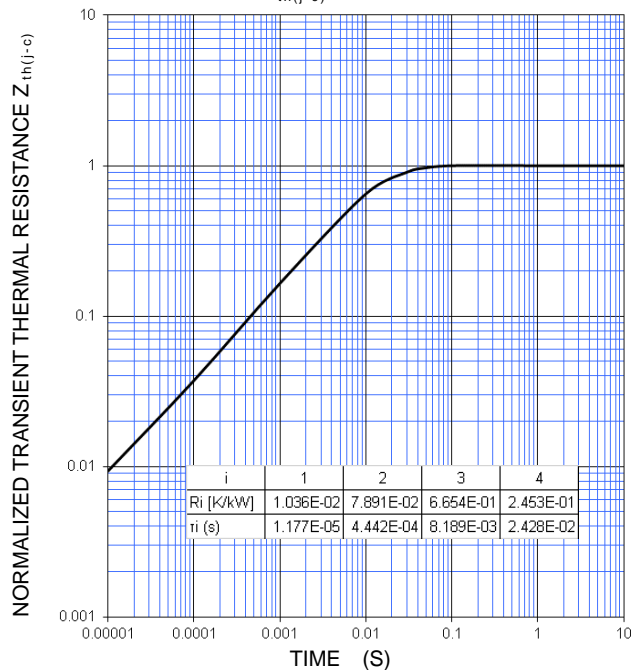
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RM800DY-34S

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PERFORMANCE CURVES

**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
 (MAXIMUM)**

Single pulse, $T_C=25\text{ }^\circ\text{C}$
 $R_{th(j-c)}=20\text{ K/kW}$



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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